

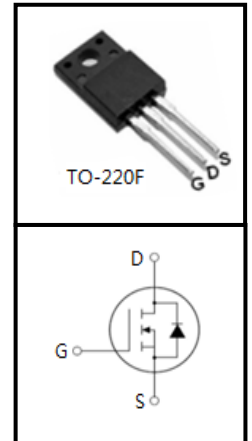
1000V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information		
Device	Package	Marking
CS2N100LF	TO-220F	CS2N100LF

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted			
Parameter	Symbol	Value	Unit
		TO-220F	
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	1000	V
Continuous Drain Current	I_D	1.5	A
Pulsed Drain Current (note1)	I_{DM}	6	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulse Avalanche Energy (note2)	E_{AS}	90	mJ
Avalanche Current (note1)	I_{AS}	3	A
Repetitive Avalanche Energy (note1)	E_{AR}	54	mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	36	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
		TO-220F	
Thermal Resistance, Junction-to-Case	R_{thJC}	3.47	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	

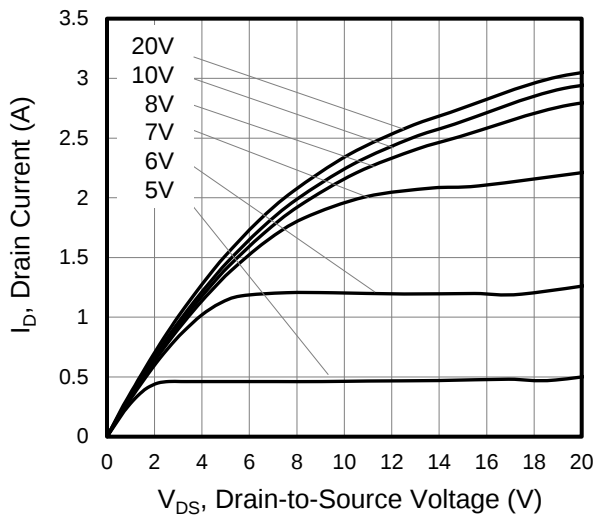
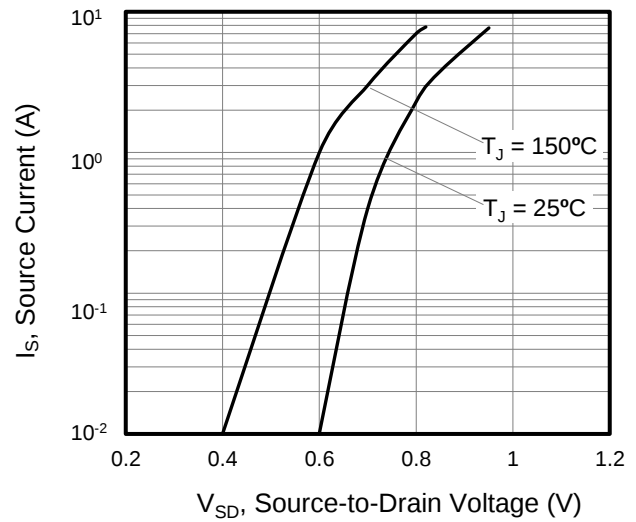
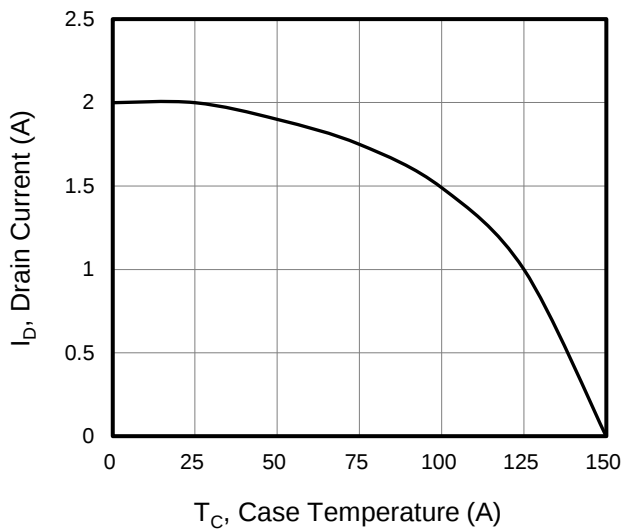
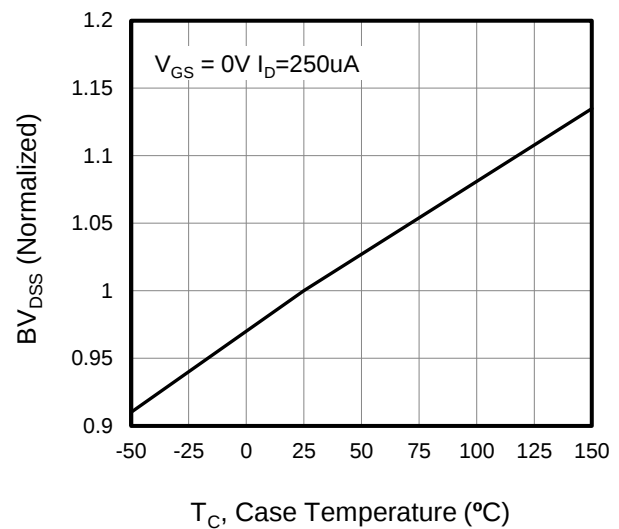
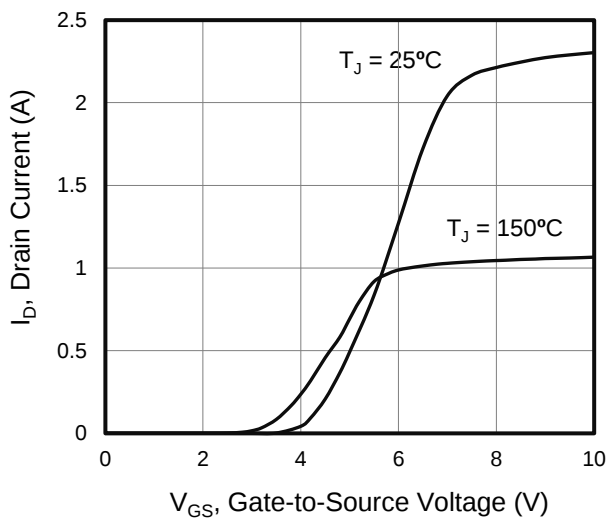
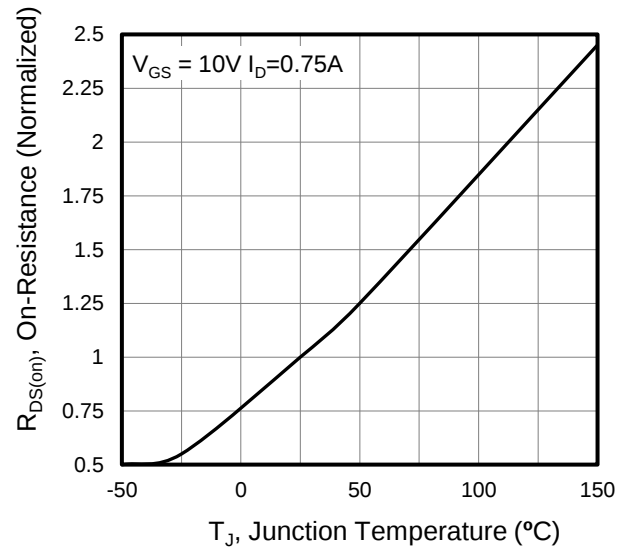
Specifications $T_J = 25^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	1000	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 1000V, V _{GS} = 0V, T _J = 25°C	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	R _{DS(on)}	V _{GS} = 10V, I _D = 0.75A	--	8	9.6	Ω
Dynamic						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1.0MHz	--	308	--	pF
Output Capacitance	C _{oss}		--	32	--	
Reverse Transfer Capacitance	C _{rss}		--	6.2	--	
Gate Resistance	R _g	V _{GS} = 0V,V _{DS} = 0V,f = 1.0MHz	--	2.2	--	Ω
Total Gate Charge	Q _g	V _{DD} = 800V, I _D = 1.5A, V _{GS} = 15V	--	16	--	nC
Gate-Source Charge	Q _{gs}		--	2	--	
Gate-Drain Charge	Q _{gd}		--	10	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 500V, I _D =1.5A, R _G = 25 Ω	--	34	--	ns
Turn-on Rise Time	t _r		--	12	--	
Turn-off Delay Time	t _{d(off)}		--	80	--	
Turn-off Fall Time	t _f		--	45	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25 °C	--	--	2	A
Pulsed Diode Forward Current	I _{SM}		--	--	8	
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 0.75A, V _{GS} = 0V	--	--	1.4	V
Reverse Recovery Time	t _{rr}	V _R = 500V,I _S = 1.5A, di _F /dt =100A /μs	--	590	--	ns
Reverse Recovery Charge	Q _{rr}		--	2.34	--	uC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 20.0mH, V_{DD} = 90V, R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

Figure 2. Body Diode Forward Voltage

Figure 3. Drain Current vs. Temperature

Figure 4. BV_{DSS} Variation vs. Temperature

Figure 5. Transfer Characteristics

Figure 6. On-Resistance vs. Temperature


Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Capacitance

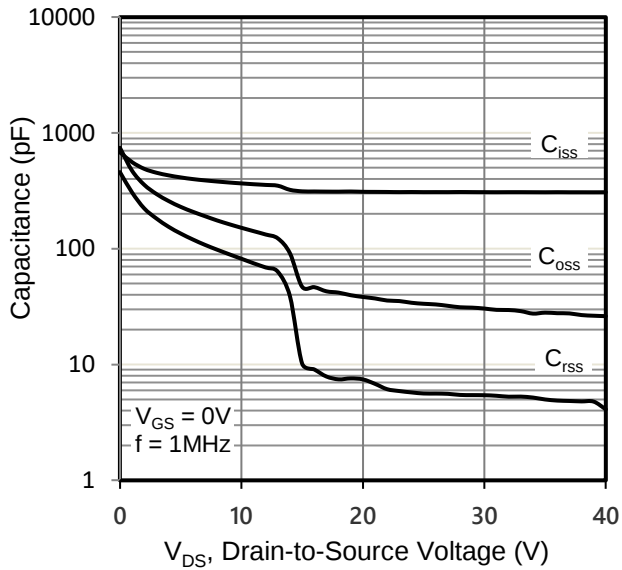
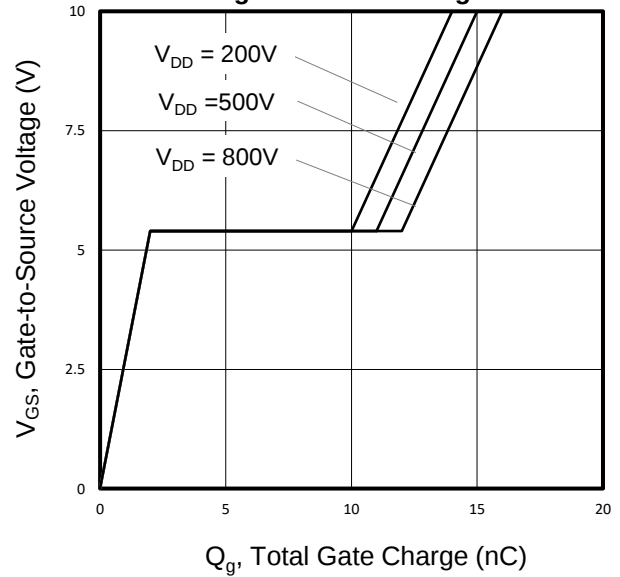


Figure 8. Gate Charge



**Figure 9. Transient Thermal Impedance
TO-220F**

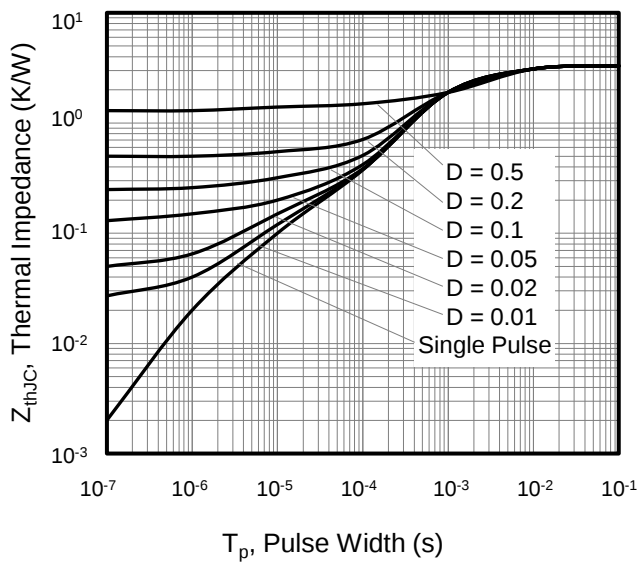


Figure A: Gate Charge Test Circuit and Waveform

Figure B: Resistive Switching Test Circuit and Waveform

Figure C: Unclamped Inductive Switching Test Circuit and Waveform


TO-220F



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